

N-channel 80 V, 25 mΩ logic level MOSFET in LFPAK56 14 April 2016 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product is designed and qualified for use in a wide range of power supply & motor control equipment.

2. Features and benefits

- Advanced TrenchMOS provides low R_{DSon} and low gate charge
- Logic level gate operation
- Avalanche rated, 100% tested
- LFPAK provides maximum power density in a Power SO8 package

3. Applications

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- Synchronous rectification in power supply equipment
- Chargers & adaptors with V_{out} < 10 V
- Fast charge & USB-PD applications
- Battery powered motor control
- LED lighting & TV backlight

4. Quick reference data

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1.1.1

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	80	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	37	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	95	W
Static char	acteristics					_
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 11</u>	-	22.2	27	mΩ
Dynamic cl	naracteristics					,
Q _{GD}	gate-drain charge	$I_D = 10 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$	-	5.8	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	a	G-UTA
4	G	gate	មុច្ចមុ	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN025-80YL	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN025-80YL	025L80

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

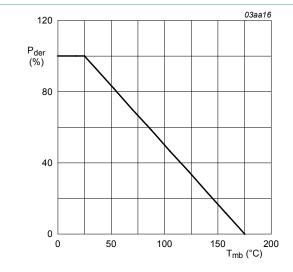
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	95	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	37	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>	-	26.5	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; <u>Fig. 3</u>	-	150	А
T _{stg}	storage temperature		-55	175	°C

N-channel 80 V, 25 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C		-	37	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	150	А
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} {\sf I}_{\sf D} = 37 \; {\sf A}; \; {\sf V}_{sup} \le 80 \; {\sf V}; \; {\sf R}_{GS} = 50 \; \Omega; \\ {\sf V}_{GS} = 5 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {}^{\circ}{\sf C}; \; unclamped; \\ \hline {\sf Fig. 4} \end{array}$	[1][2]	-	45.4	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^\circ$ C.

[2] Refer to application note AN10273 for further information.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

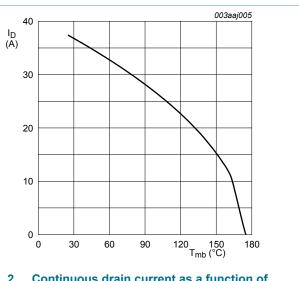
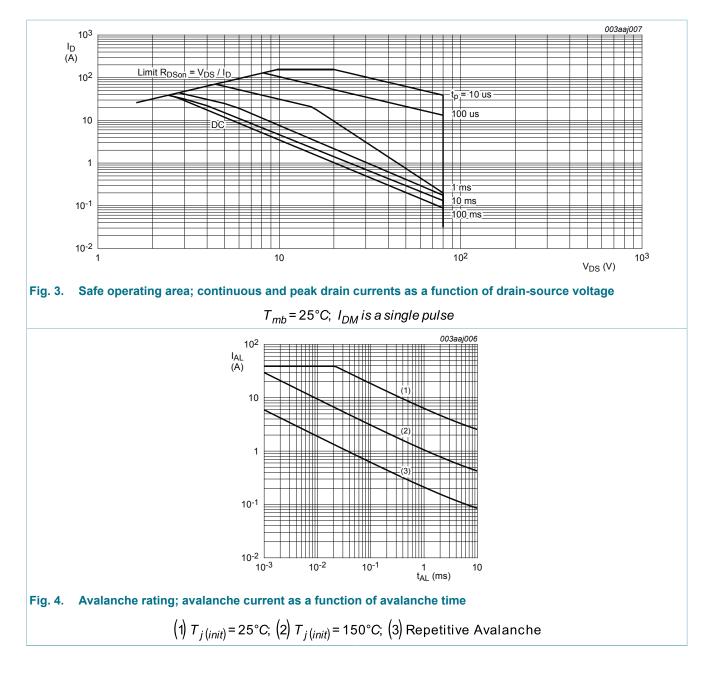


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$

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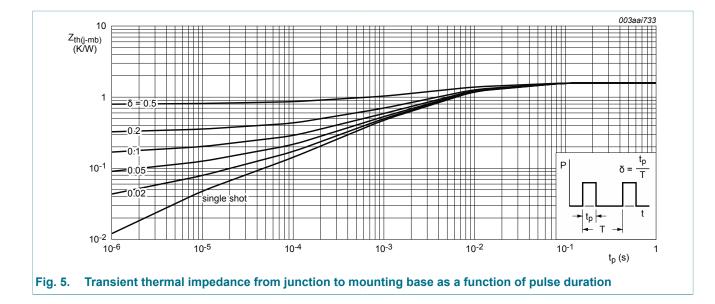


9. Thermal characteristics

Table 6. Thermal characteristics								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5		-	-	1.58	K/W	

PSMN025-80YL

N-channel 80 V, 25 m Ω logic level MOSFET in LFPAK56



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	72	-	-	V
V _{GS(th)} gate-source thre voltage	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9;</u> Fig. 10	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 9</u>	-	-	2.45	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	0.5	-	-	V
I _{DSS} d	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.1	1	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 11</u>	-	22.2	27	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	20.5	25	mΩ
		V _{GS} = 5 V; I _D = 10 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	67.8	mΩ
Dynamic ch	aracteristics	· · · · ·			_	
Q _{G(tot)}	total gate charge	I_D = 10 A; V_{DS} = 64 V; V_{GS} = 5 V; T _j = 25 °C; Fig. 13; Fig. 14	-	17.1	-	nC
		I _D = 10 A; V _{DS} = 64 V; V _{GS} = 10 V; T _i = 25 °C; Fig. 13; Fig. 14	-	34.3	-	nC

PSMN025-80YL

N-channel 80 V, 25 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions	N	Min	Тур	Мах	Unit
Q _{GS}	gate-source charge	I_D = 10 A; V_{DS} = 64 V; V_{GS} = 5 V;	-	-	5.2	-	nC
Q _{GD}	gate-drain charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	-	5.8	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	-	2032	2703	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	-	147	176	pF
C _{rss}	reverse transfer capacitance			-	75	103	pF
t _{d(on)}	turn-on delay time	V_{DS} = 60 V; R _L = 4.98 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C	-	-	11.6	-	ns
t _r	rise time		-	-	17.2	-	ns
t _{d(off)}	turn-off delay time		-	-	23.9	-	ns
t _f	fall time	1		-	15.3	-	ns
Source-dra	ain diode				I	1	
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	-	0.81	1.2	V
t _{rr}	reverse recovery time	I_{S} = 10 A; dI_{S}/dt = -100 A/µs; V_{GS} = 0 V;	-	-	23.8	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	-	27	-	nC

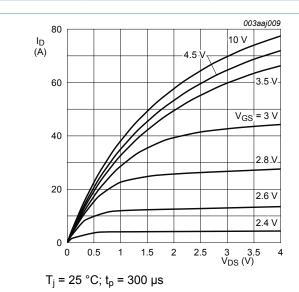


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

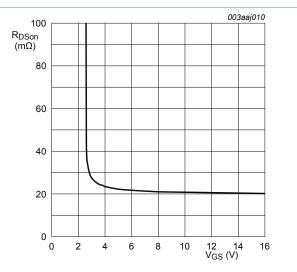
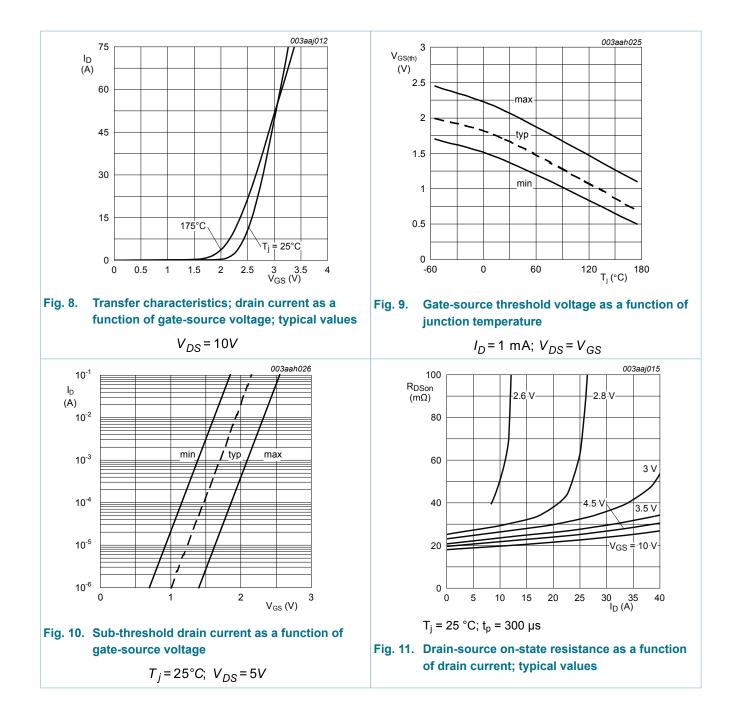


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 10A$

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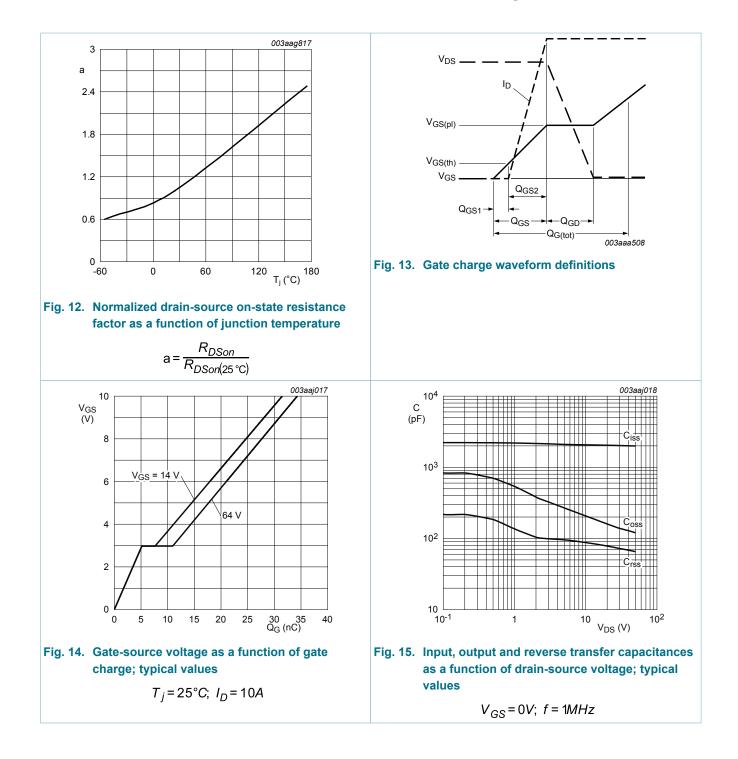
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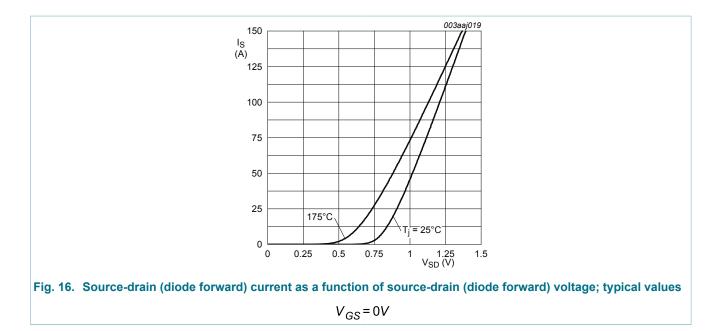


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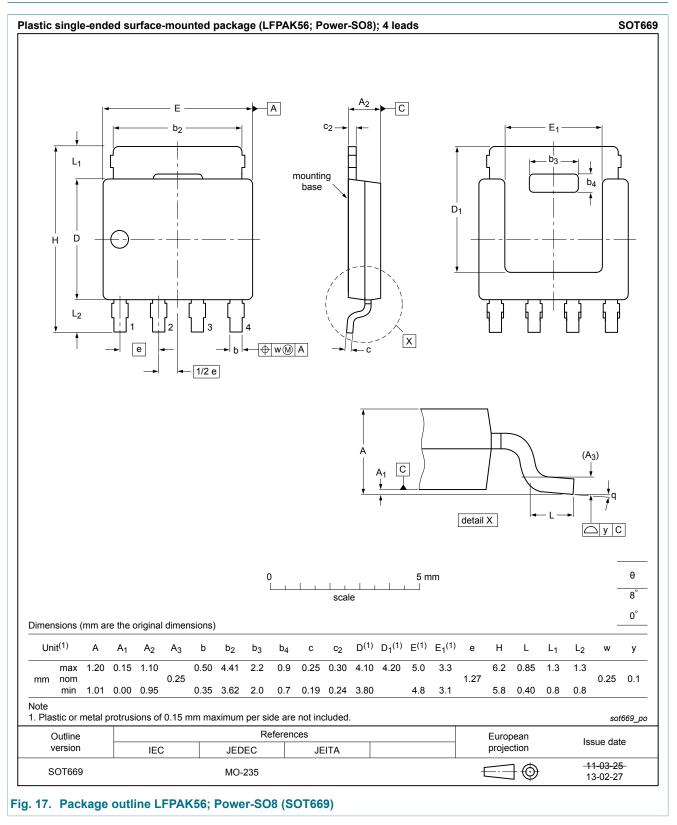
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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N-channel 80 V, 25 m Ω logic level MOSFET in LFPAK56

13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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